

Comments and Corrections

Correction to “Recent Advances in Avalanche Photodiodes”

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In [1], the graphic in Fig.10 was incorrect. Therefore, in Figs. 11–18, the captions did not match the correct figures. The following are the figures with the correct captions.

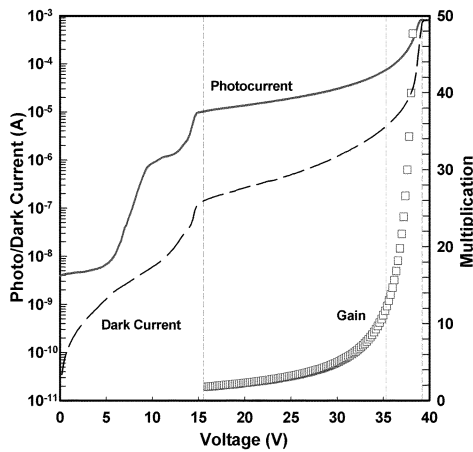


Fig. 10. Photocurrent, dark current, and gain curves for an $\text{Al}_{0.48}\text{In}_{0.52}\text{As}/\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ SACM APD.

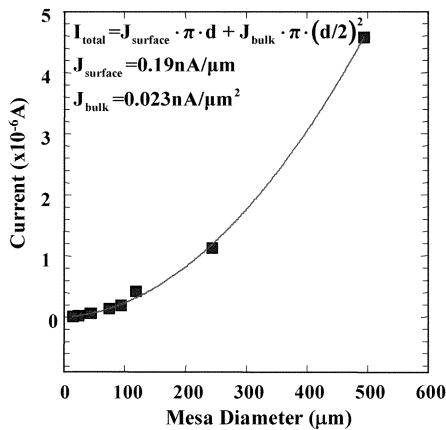


Fig. 11. Measured dark current and quadratic fit versus mesa diameter for $\text{Al}_{0.48}\text{In}_{0.52}\text{As}/\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ SACM APDs.

Manuscript received December 13, 2004.
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 Digital Object Identifier 10.1109/JSTQE.2004.842288

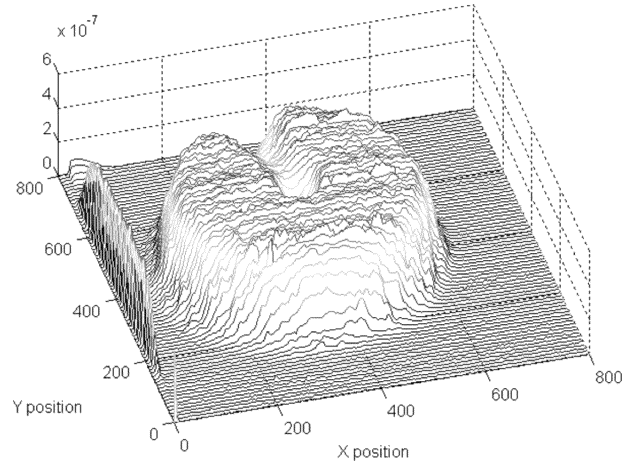


Fig. 12. Raster scan of photoresponse of a $500\text{-}\mu\text{m}$ -diameter $\text{Al}_{0.48}\text{In}_{0.52}\text{As}/\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ SACM APD for $M \sim 20$.

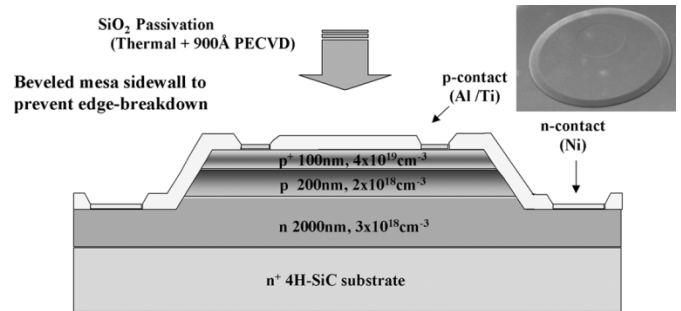


Fig. 13. Schematic cross section of 4H-SiC APD. The inset shows an SEM photograph of the etched mesa.

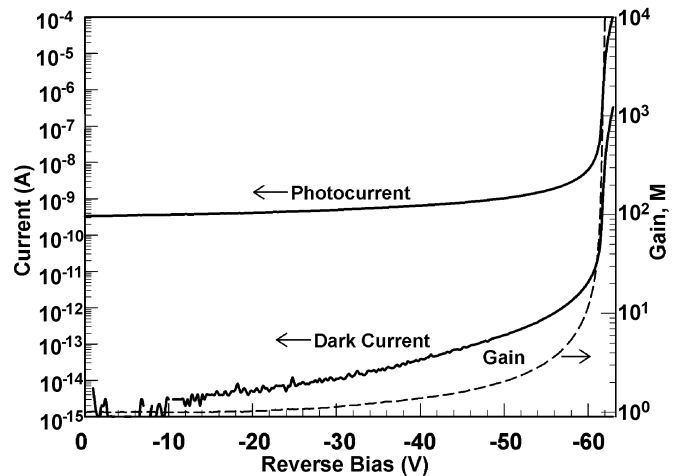


Fig. 14. Photocurrent, dark current, and gain of $100\text{-}\mu\text{m}$ -diameter 4H-SiC APD.

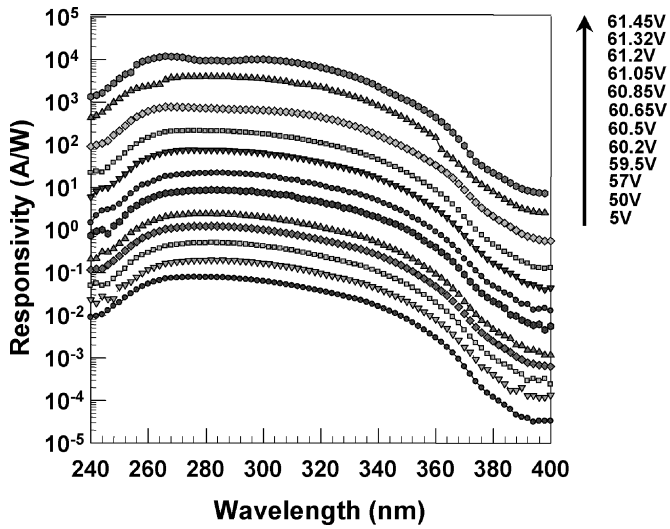


Fig. 15. Spectral response of 4H-SiC APD for a range of bias voltages.

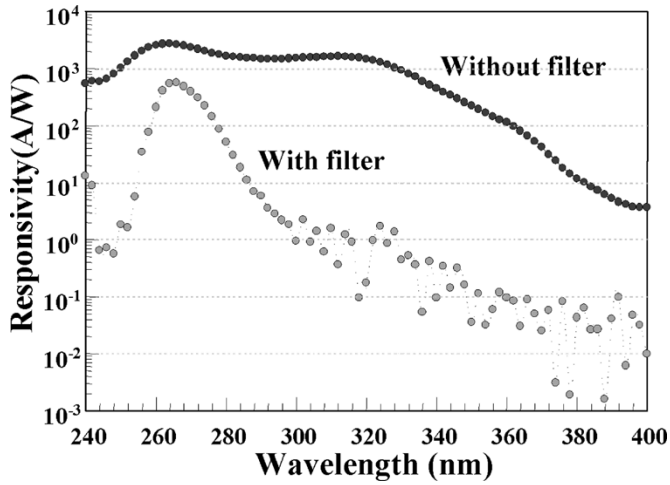


Fig. 16. Responsivity of 4H-SiC APD with and without a 266-nm "laser line" filter.

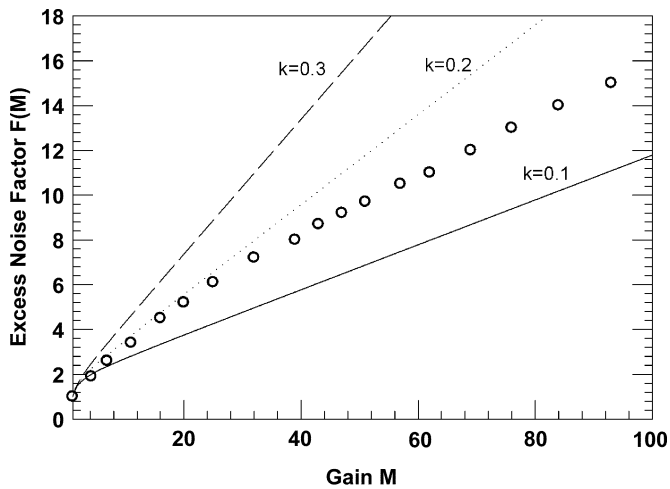


Fig. 18. Measured excess noise, $F(M)$, of a SiC APD versus gain, M . The excess noise corresponds to a k value of 0.15.

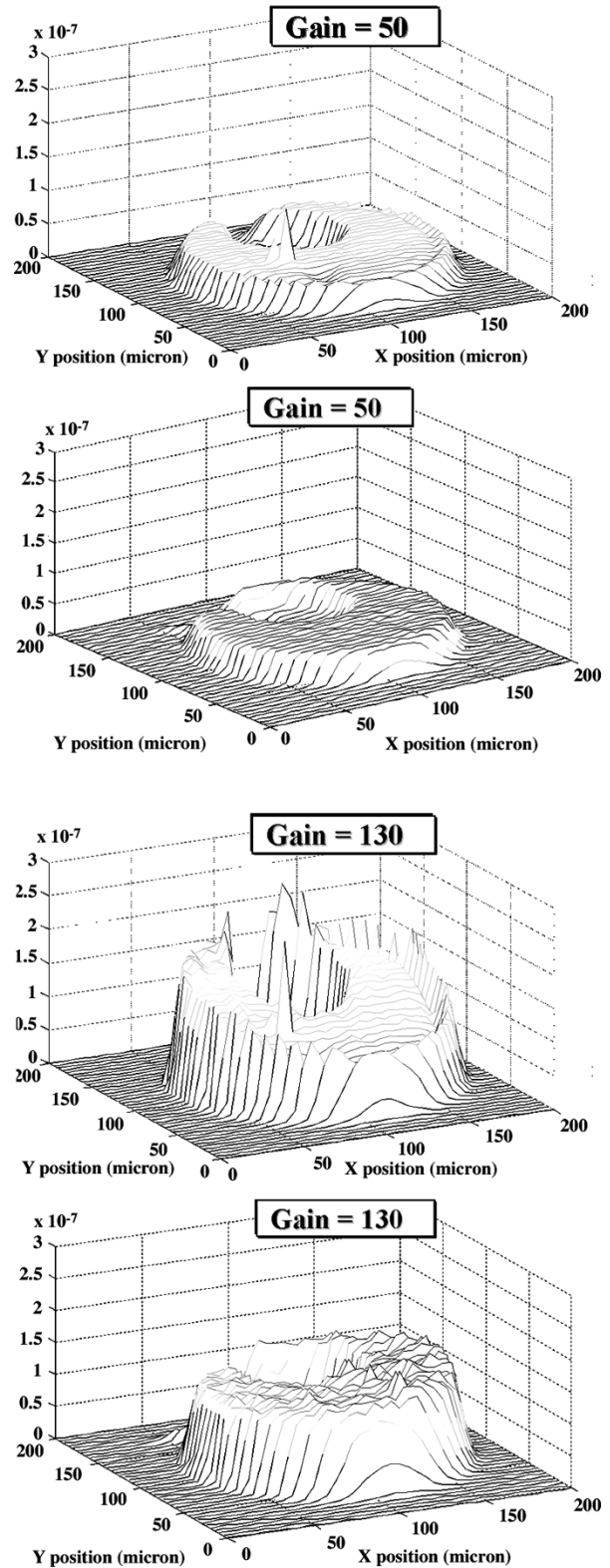


Fig. 17. Raster scans of the photocurrent of (a) nonbeveled and (b) beveled mesa-structure SiC APDs.

REFERENCES

[1] J. C.J. C. Campbell, S.Stephane Demiguel, F.F. Ma, A.A. Beck, X.X. Guo, S.S. Wang, X.X. Zheng, X.X. Li, J. D.J. D. Beck, M. A.M. A. Kinch, A.A. Huntington, L. A.L. A. Coldren, J.Jean Decobert, and N.Nadine Tschertner, "Recent advances in avalanche photodiodes," *IEEE J. Select Topics Quantum Electron.*, vol. 10, pp. 777-787, July/Aug. 2004.